

TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

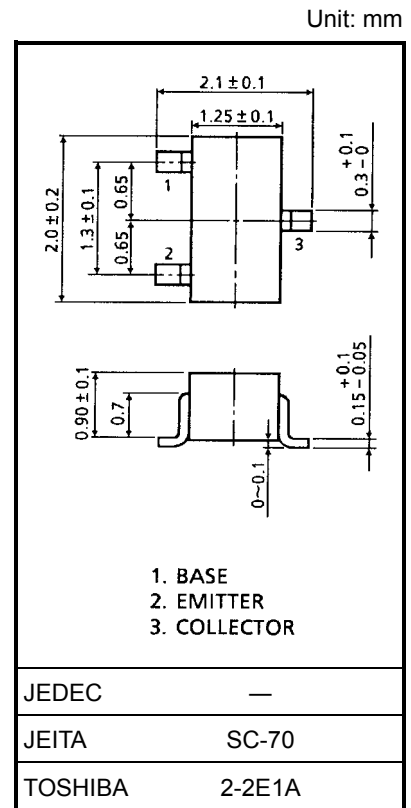
2SC5085

VHF~UHF Band Low Noise Amplifier Applications

- Low noise figure, high gain.
- $NF = 1.1\text{dB}$, $|S_{21e}|^2 = 11\text{dB}$ ($f = 1\text{GHz}$)

Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	20	V
Collector-emitter voltage	V_{CEO}	12	V
Emitter-base voltage	V_{EBO}	3	V
Base current	I_B	40	mA
Collector current	I_C	80	mA
Collector power dissipation	P_C	100	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55~125	$^\circ\text{C}$



Microwave Characteristics ($T_a = 25^\circ\text{C}$)

Weight: 0.006 g (typ.)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Transition frequency	f_T	$V_{CE} = 10\text{V}$, $I_C = 20\text{mA}$	5	7	—	GHz
Insertion gain	$ S_{21e} ^2 (1)$	$V_{CE} = 10\text{V}$, $I_C = 20\text{mA}$, $f = 500\text{MHz}$	—	16.5	—	dB
	$ S_{21e} ^2 (2)$	$V_{CE} = 10\text{V}$, $I_C = 20\text{mA}$, $f = 1\text{GHz}$	7.5	11	—	
Noise figure	NF (1)	$V_{CE} = 10\text{V}$, $I_C = 5\text{mA}$, $f = 500\text{MHz}$	—	1	—	dB
	NF (2)	$V_{CE} = 10\text{V}$, $I_C = 5\text{mA}$, $f = 1\text{GHz}$	—	1.1	2	

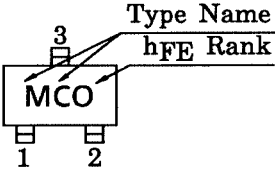
Electrical Characteristics ($T_a = 25^\circ\text{C}$)

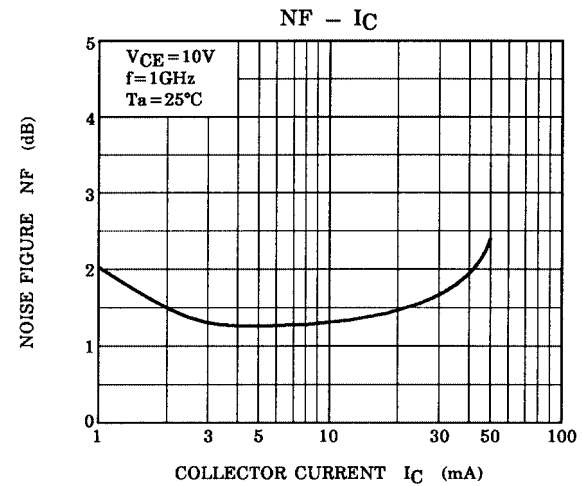
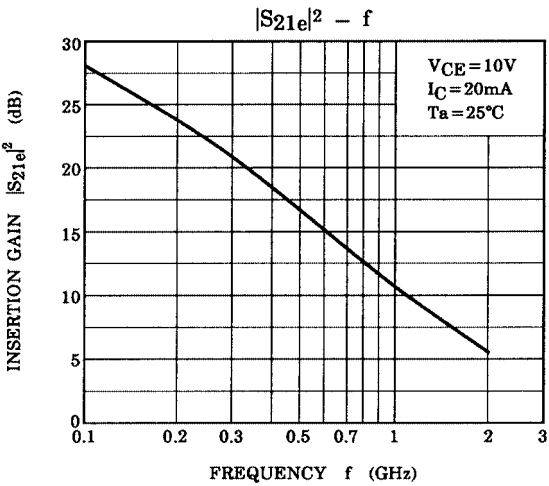
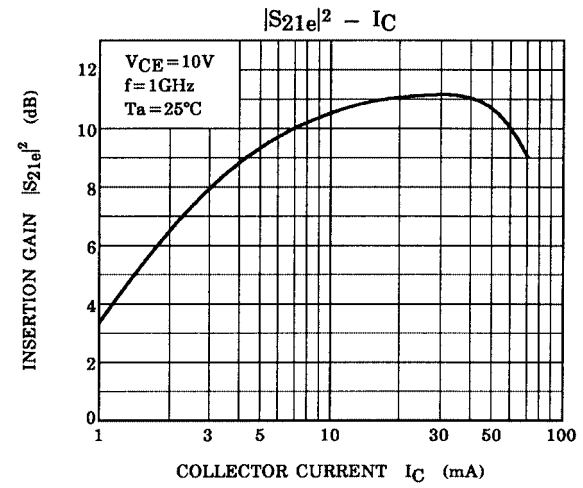
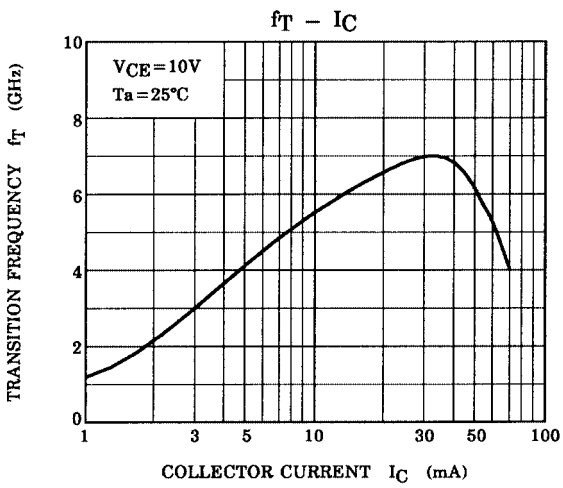
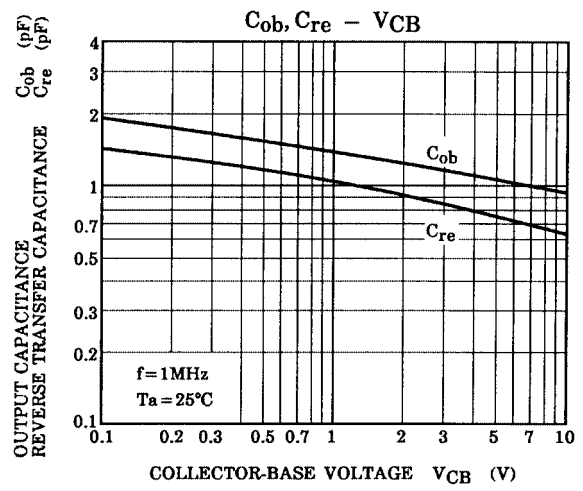
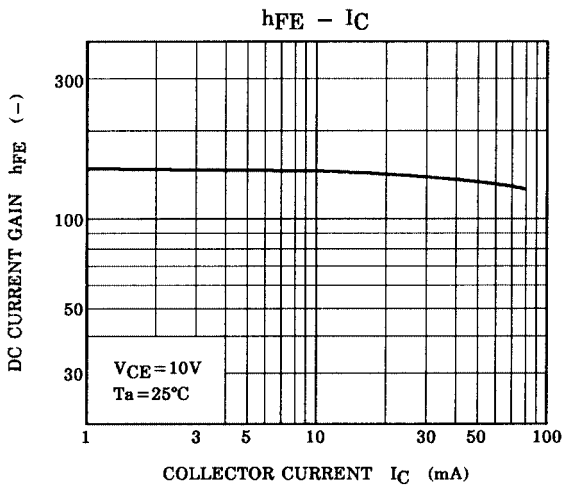
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 10\text{V}$, $I_E = 0$	—	—	1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 1\text{V}$, $I_C = 0$	—	—	1	μA
DC current gain	h_{FE} (Note 1)	$V_{CE} = 10\text{V}$, $I_C = 20\text{mA}$	80	—	240	
Output capacitance	C_{ob}	$V_{CB} = 10\text{V}$, $I_E = 0$, $f = 1\text{MHz}$ (Note 2)	—	1.0	—	pF
Reverse transfer capacitance	C_{re}		—	0.65	1.15	pF

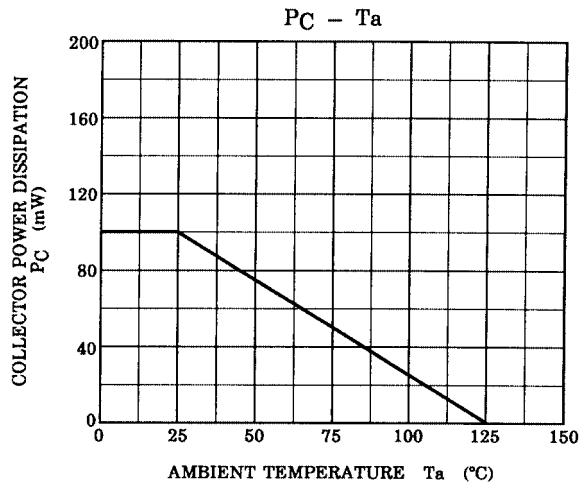
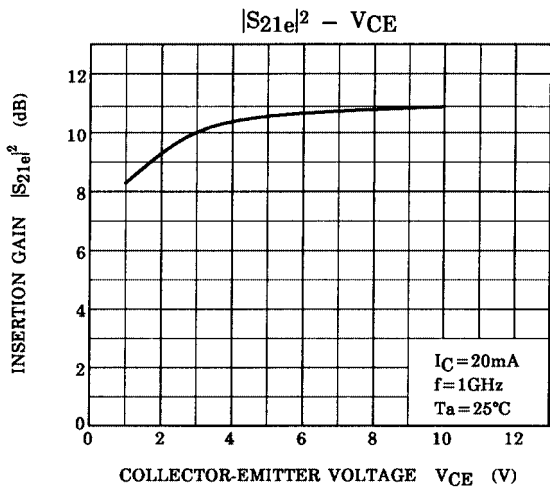
Note 1: h_{FE} classification O: 80~160, Y: 120~240

Note 2: C_{re} is measured by 3 terminal method with capacitance bridge.

Marking







S-Parameter $Z_O = 50 \Omega, T_a = 25^\circ\text{C}$

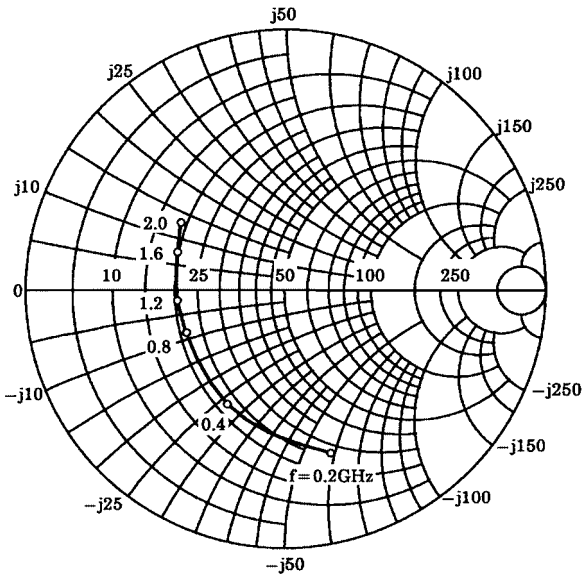
$V_{CE} = 10 \text{ V}, I_C = 5 \text{ mA}$

Frequency (MHz)	S11		S21		S12		S22	
	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.
200	0.672	-73.0	9.460	128.6	0.052	53.6	0.707	-31.3
400	0.498	-115.9	6.268	105.9	0.068	46.8	0.513	-36.2
600	0.443	-141.7	4.554	93.3	0.078	49.0	0.437	-36.6
800	0.426	-158.7	3.556	84.5	0.088	53.2	0.401	-36.8
1000	0.422	-171.9	2.948	77.5	0.099	57.9	0.383	-38.3
1200	0.428	177.5	2.526	71.1	0.113	62.7	0.373	-40.6
1400	0.437	168.3	2.240	65.5	0.133	65.8	0.367	-43.9
1600	0.449	159.9	1.997	60.1	0.152	67.6	0.362	-48.2
1800	0.464	153.1	1.821	55.0	0.171	68.7	0.358	-52.8
2000	0.485	146.7	1.686	50.9	0.195	70.6	0.350	-57.6

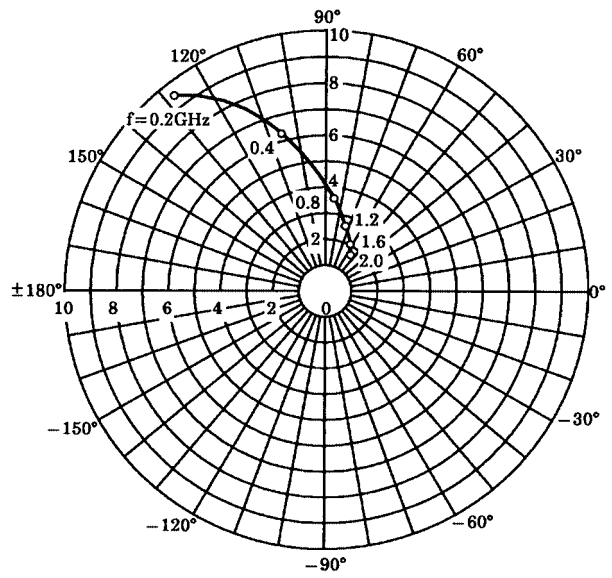
$V_{CE} = 10 \text{ V}, I_C = 20 \text{ mA}$

Frequency (MHz)	S11		S21		S12		S22	
	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.
200	0.392	-116.4	16.247	109.3	0.034	59.7	0.420	-43.7
400	0.329	-152.1	8.775	94.5	0.054	66.0	0.280	-38.4
600	0.321	-170.6	6.018	86.3	0.075	69.5	0.244	-33.7
800	0.321	177.5	4.598	80.2	0.097	70.7	0.231	-31.7
1000	0.324	167.9	3.767	74.8	0.119	71.2	0.225	-31.3
1200	0.332	160.3	3.191	70.0	0.142	71.3	0.225	-32.7
1400	0.341	153.5	2.812	65.2	0.168	70.0	0.225	-36.2
1600	0.352	146.6	2.502	60.7	0.190	68.4	0.222	-40.3
1800	0.362	142.2	2.264	56.5	0.212	66.8	0.217	-44.9
2000	0.379	137.7	2.092	52.8	0.236	66.3	0.212	-49.4

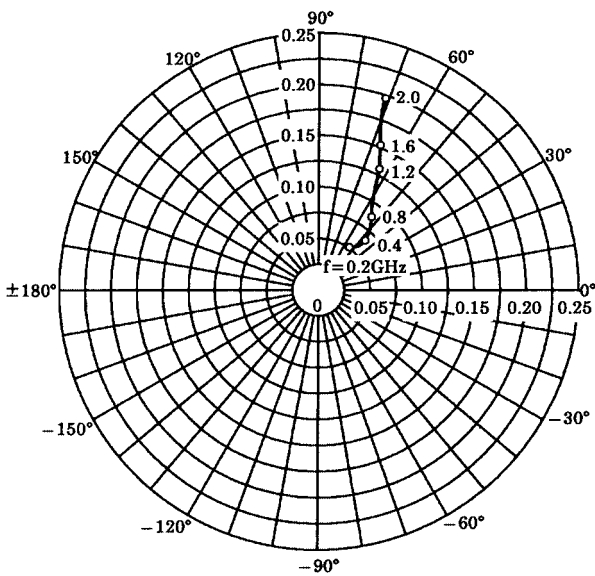
S_{11e}
V_{CE} = 10V
I_C = 5mA
T_a = 25°C
 (UNIT : Ω)



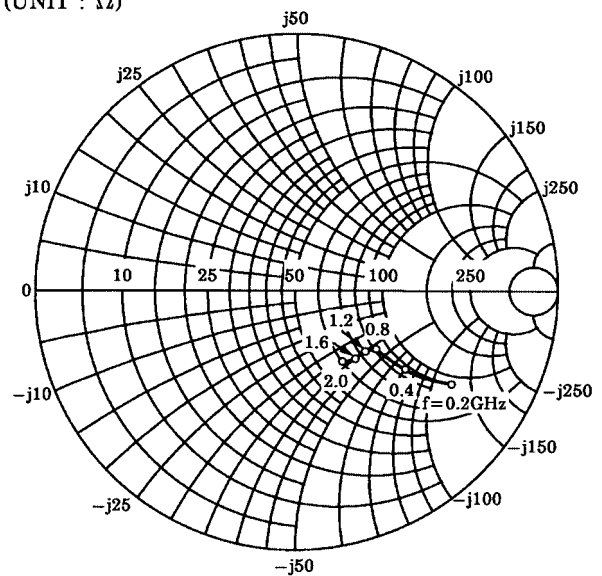
S_{21e}
V_{CE} = 10V
I_C = 5mA
T_a = 25°C



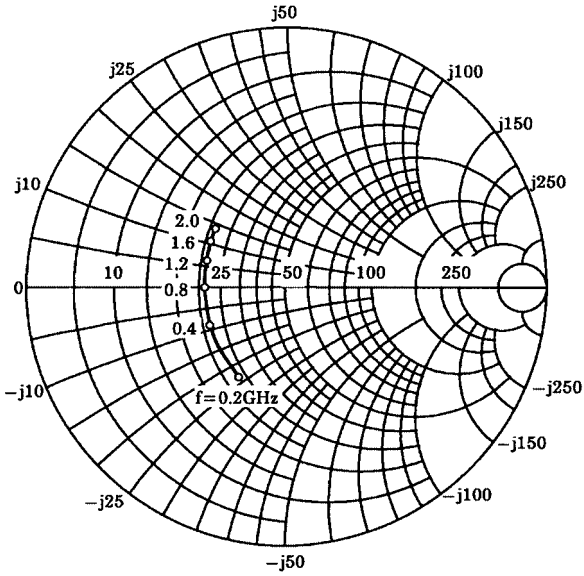
S_{12e}
V_{CE} = 10V
I_C = 5mA
T_a = 25°C



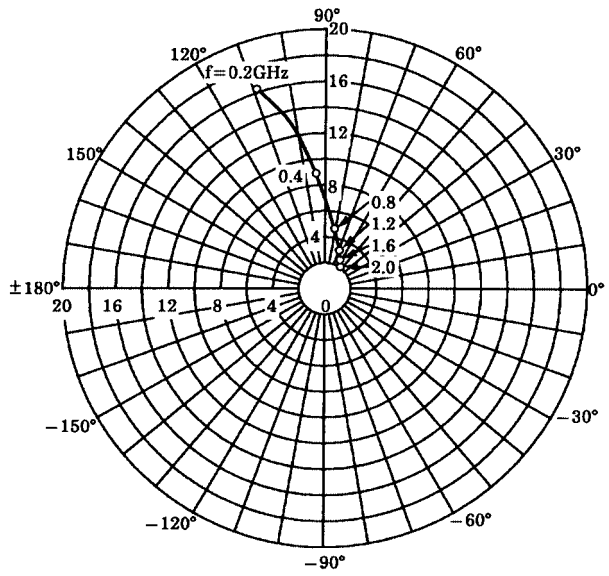
S_{22e}
V_{CE} = 10V
I_C = 5mA
T_a = 25°C
 (UNIT : Ω)



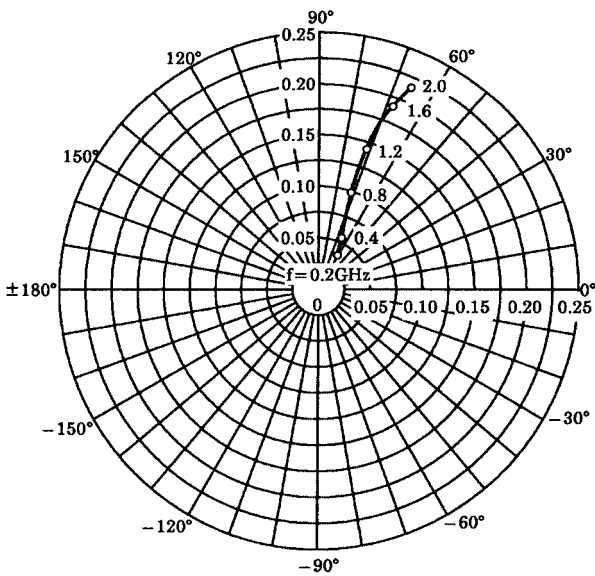
S11e
VCE = 10V
IC = 20mA
Ta = 25°C
(UNIT : Ω)



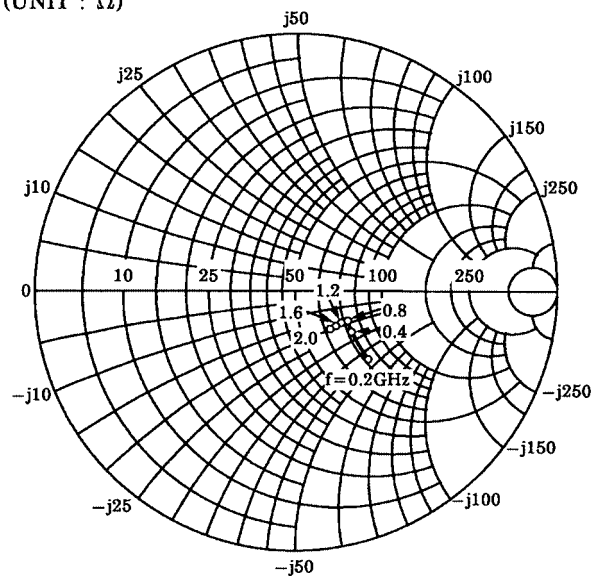
S21e
VCE = 10V
IC = 20mA
Ta = 25°C



S12e
VCE = 10V
IC = 20mA
Ta = 25°C



S22e
VCE = 10V
IC = 20mA
Ta = 25°C
(UNIT : Ω)



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